

IN THE ABSTRACT

Please replace the abstract of the invention with the following:

--The present invention relates to a method for fabricating a conducting layer pattern using a hard mask of which an upper surface is flattened by the use of ArF exposure light source. The method includes the steps of: forming a conducting layer on a semiconductor substrate; forming hard mask layers on the conducting layer; forming a photoresist pattern on the hard mask layers using an ArF exposure light source in order to form a predetermined pattern; forming a first hard mask pattern by etching a second hard mask layer using the photoresist pattern as an etching mask; etching a first hard mask layer and forming a second hard mask pattern, thereby forming a first resulting structure; depositing an insulation layer on the first resulting structure; and patterning the conducting layer using the second hard mask pattern as an etching mask.--